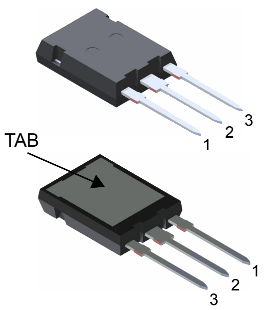
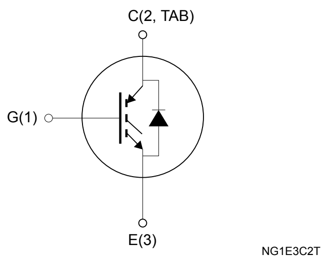
STGYA120M65DF2

Datasheet

Trench gate field-stop, 650 V, 120 A, low-loss M series IGBT in a Max247 long leads package



Max247 long leads



Product status link
STGYA120M65DF2

Product summary	
Order code	STGYA120M65DF2
Marking	G120M65DF2
Package	Max247 long leads
Packing	Tube

Features

- Maximum junction temperature: T_J = 175 °C
- 6 µs of minimum short-circuit withstand time
- $V_{CE(sat)}$ = 1.65 V (typ.) @ I_C = 120 A
- Tight parameter distribution
- Safer paralleling
- Positive $V_{CE(sat)}$ temperature coefficient
- Low thermal resistance
- Soft- and fast-recovery antiparallel diode

Applications

- Motor control
- UPS
- PFC
- General purpose inverter

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where the low-loss and the short-circuit functionality is essential. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and the tight parameter distribution result in safer paralleling operation.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0 V)	650	V
I_C	Continuous collector current at T_C = 25 °C	160	A
	Continuous collector current at T_C = 100 °C	120	
I_{CP} (1)	Pulsed collector current	360	A
V_{GE}	Gate-emitter voltage	±20	V
I_F	Continuous forward current at T_C = 25 °C	160	A
	Continuous forward current at T_C = 100 °C	120	
I_{FP} (1)	Pulsed forward current	360	A
P_{TOT}	Total power dissipation at T_C = 25 °C	625	W
T_{STG}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range	-55 to 175	°C

1. *Pulse width is limited by maximum junction temperature.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case IGBT	0.24	°C/W
	Thermal resistance, junction-to-case diode	0.6	
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

T_J = 25 °C unless otherwise specified.

Table 3. **Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 250 µA	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 120 A		1.65	2.15	V
		V_{GE} = 15 V, I_C = 120 A, T_J = 125 °C		1.95		
		V_{GE} = 15 V, I_C = 120 A, T_J = 175 °C		2.1		
V_F	Forward on-voltage	I_F = 120 A		1.9	2.6	V
		I_F = 120 A, T_J = 125 °C		1.7		
		I_F = 120 A, T_J = 175 °C		1.6		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 2 mA	5	6	7	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 650 V			100	µA
I_{GES}	Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = ±20 V			±250	nA

Table 4. **Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	11	-	nF
C_{oes}	Output capacitance		-	0.61	-	nF
C_{res}	Reverse transfer capacitance		-	0.25	-	nF
Q_g	Total gate charge	V_{CC} = 520 V, I_C = 120 A, V_{GE} = 0 to 15 V (see Figure 30. Gate charge test circuit)	-	420	-	nC
Q_{ge}	Gate-emitter charge		-	90	-	nC
Q_{gc}	Gate-collector charge		-	160	-	nC

Table 5. IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{CE} = 400 V, I_C = 120 A, V_{GE} = 15 V, R_G = 4.7 Ω (see Figure 29. Test circuit for inductive load switching)		66	-	ns
t_r	Current rise time			38	-	ns
$(di/dt)_{on}$	Turn-on current slope			2500	-	A/μs
$t_{d(off)}$	Turn-off delay time			185	-	ns
t_f	Current fall time			85	-	ns
E_{on}[(1)]	Turn-on switching energy			1.8	-	mJ
E_{off}[(2)]	Turn-off switching energy			4.41	-	mJ
E_{ts}	Total switching energy			6.21	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CE} = 400 V, I_C = 120 A, V_{GE} = 15 V, R_G = 4.7 Ω, T_J = 175 °C (see Figure 29. Test circuit for inductive load switching)		62	-	ns
t_r	Current rise time			48	-	ns
$(di/dt)_{on}$	Turn-on current slope			2016	-	A/μs
$t_{d(off)}$	Turn-off delay time			187	-	ns
t_f	Current fall time			164	-	ns
E_{on}[(1)]	Turn-on switching energy			4.4	-	mJ
E_{off}[(2)]	Turn-off switching energy			6.0	-	mJ
E_{ts}	Total switching energy			10.4	-	mJ
t_{sc}	Short-circuit withstand time	V_{CC} ≤ 400 V, V_{GE} = 13 V, T_{Jstart} ≤ 150 °C	10		-	μs
		V_{CC} ≤ 400 V, V_{GE} = 15 V, T_{Jstart} ≤ 150 °C	6		-	

1. *Including the reverse recovery of the diode.*
2. *Including the tail of the collector current.*

Table 6. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	I_F = 120 A, V_R = 400 V, V_{GE} = 15 V, di/dt = 1000 A/μs (see Figure 29. Test circuit for inductive load switching)	-	202	-	ns
Q_{rr}	Reverse recovery charge		-	2.9	-	μC
I_{rrm}	Reverse recovery current		-	32.5	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	500	-	A/μs
E_{rr}	Reverse recovery energy		-	500	-	μJ
t_{rr}	Reverse recovery time	I_F = 120 A, V_R = 400 V, V_{GE} = 15 V, di/dt = 1000 A/μs, T_J = 175 °C (see Figure 29. Test circuit for inductive load switching)	-	320	-	ns
Q_{rr}	Reverse recovery charge		-	11.2	-	μC
I_{rrm}	Reverse recovery current		-	62	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	270	-	A/μs
E_{rr}	Reverse recovery energy		-	1710	-	μJ

2.1 Electrical characteristics (curves)

Figure 1. Total power dissipation vs temperature

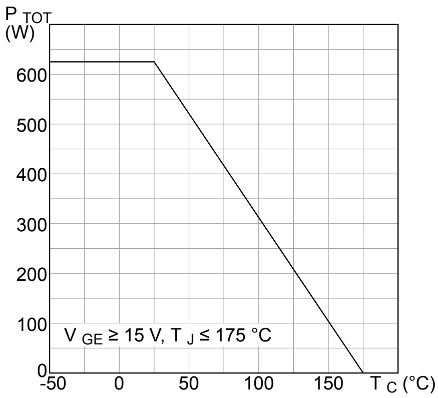


Figure 2. Collector current vs temperature

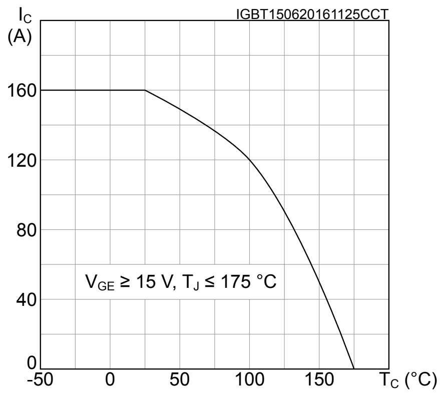


Figure 3. Typical output characteristics (T_J = 25 °C)

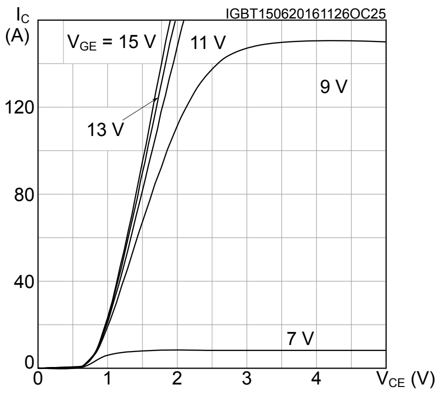


Figure 4. Typical output characteristics (T_J = 175 °C)

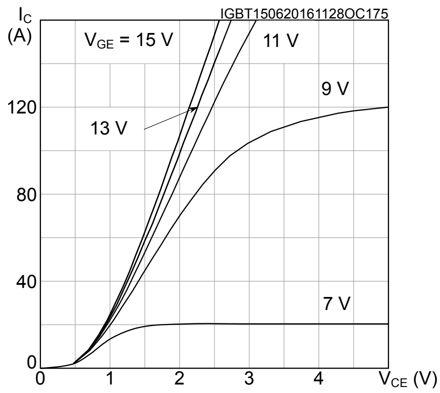


Figure 5. Typical $V_{CE(sat)}$ vs temperature

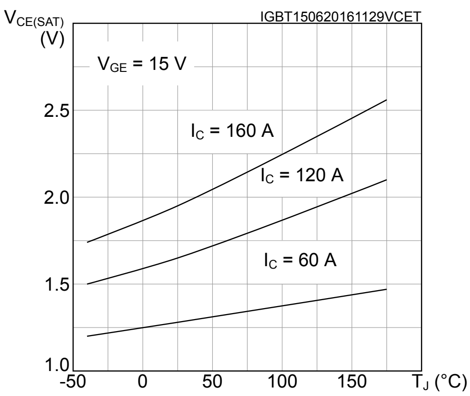


Figure 6. Typical $V_{CE(sat)}$ vs collector current

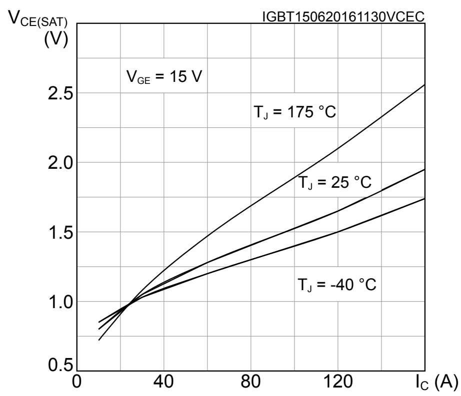


Figure 7. Collector current vs switching frequency

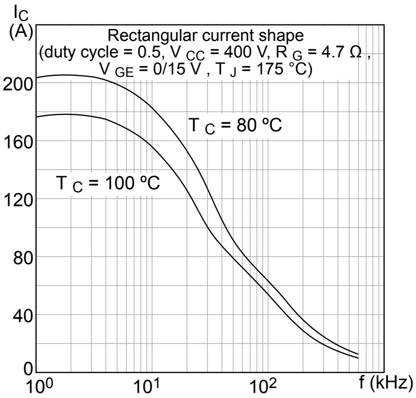


Figure 8. Forward bias safe operating area

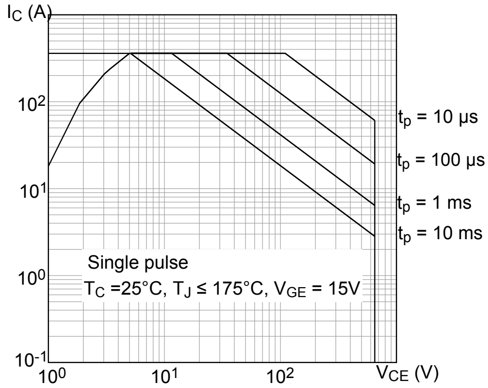


Figure 9. Typical transfer characteristics

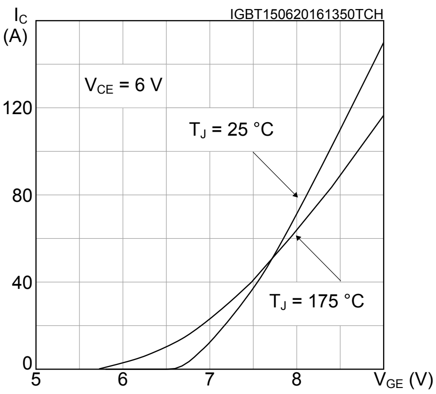


Figure 10. Typical diode V_F vs forward current

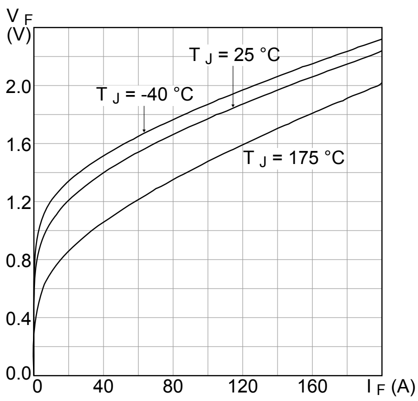


Figure 11. Normalized $V_{GE(th)}$ vs temperature

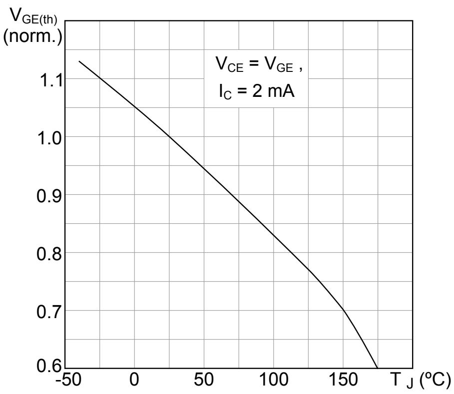


Figure 12. Normalized $V_{(BR)CES}$ vs temperature

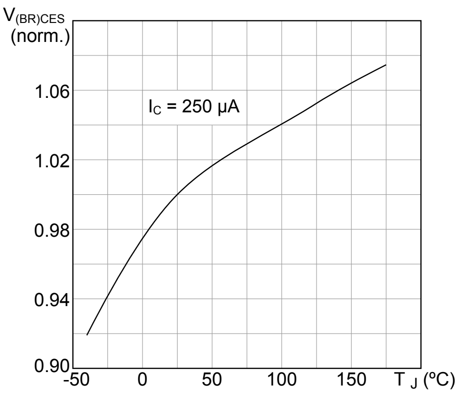


Figure 13. Typical capacitance characteristics

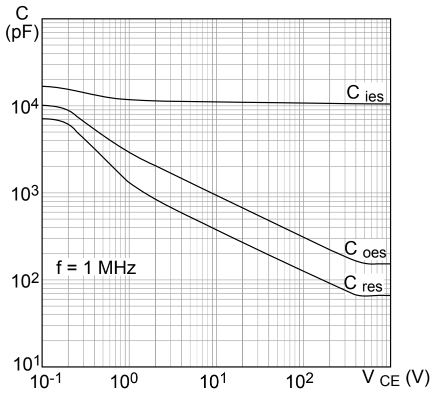


Figure 14. Typical gate charge characteristics

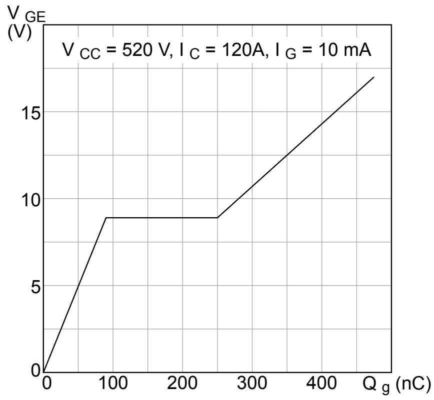


Figure 15. Typical switching energy vs collector current

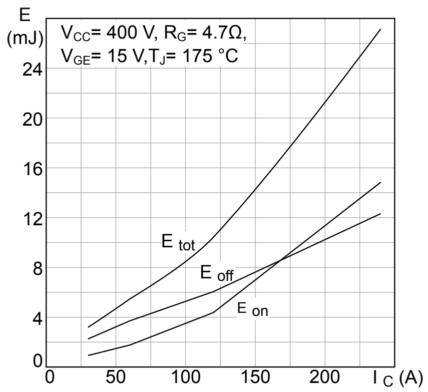


Figure 16. Typical switching energy vs R_G

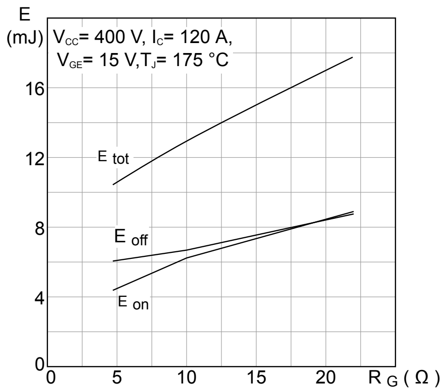


Figure 17. Typical switching energy vs temperature

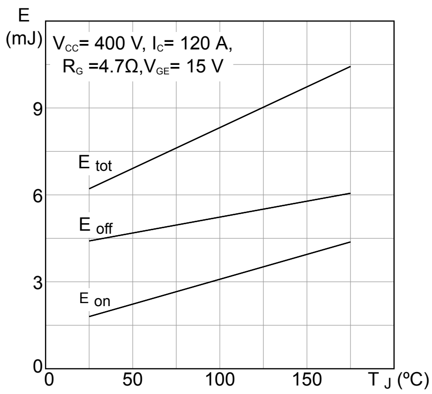


Figure 18. Typical switching energy vs collector emitter voltage

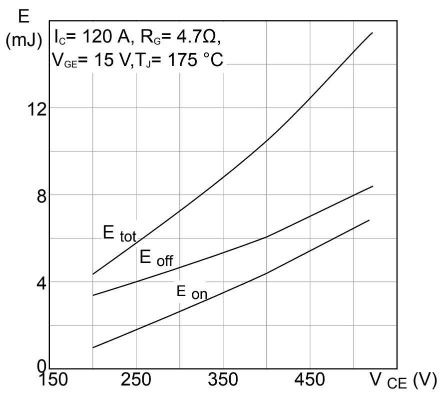


Figure 19. Short circuit time and current vs. V_{GE}

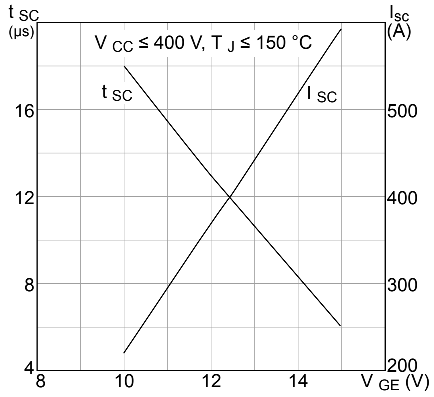


Figure 20. Typical switching times vs collector current

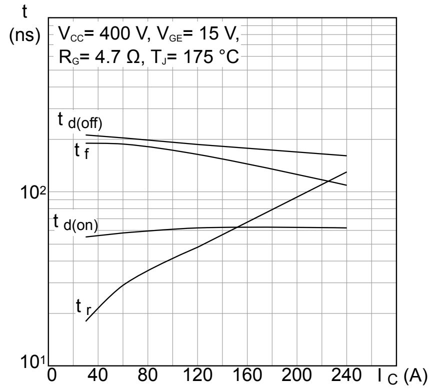


Figure 21. Typical switching times vs gate resistance

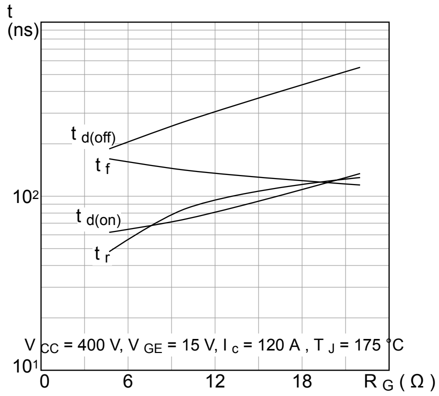


Figure 22. Typical reverse recovery current vs diode current slope

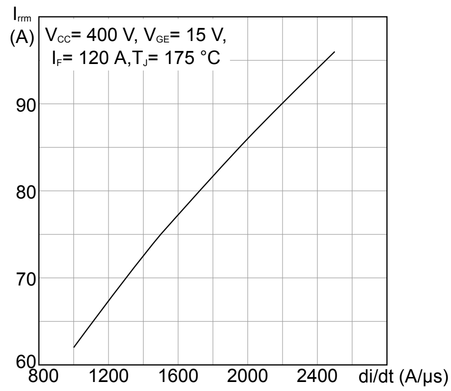


Figure 23. Typical reverse recovery time vs. diode current slope

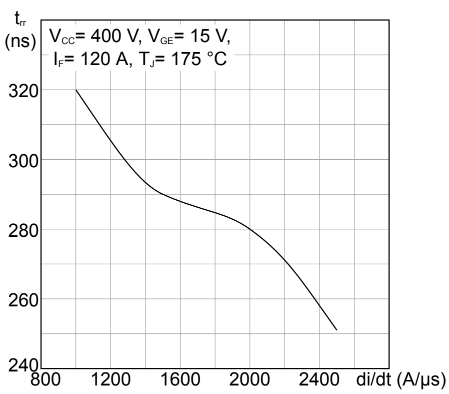


Figure 24. Typical reverse recovery charge vs diode current slope

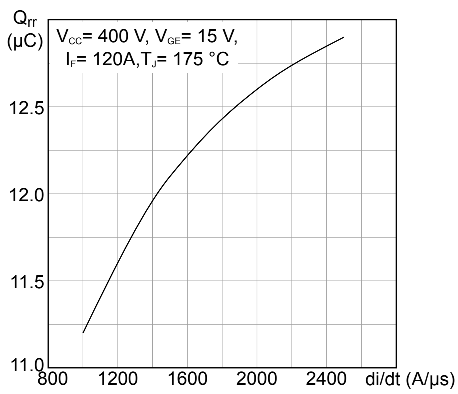


Figure 25. Typical reverse recovery energy vs diode current slope

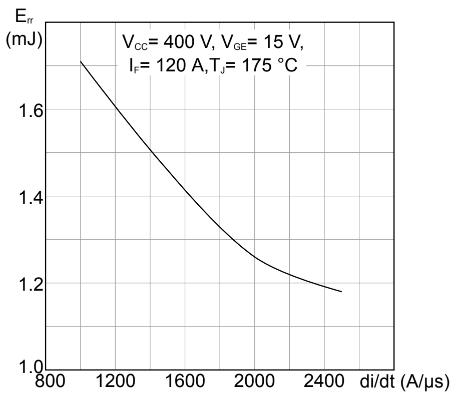


Figure 26. Normalized transient thermal impedance for IGBT

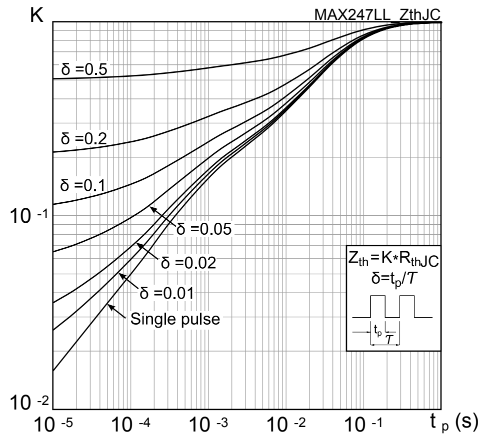
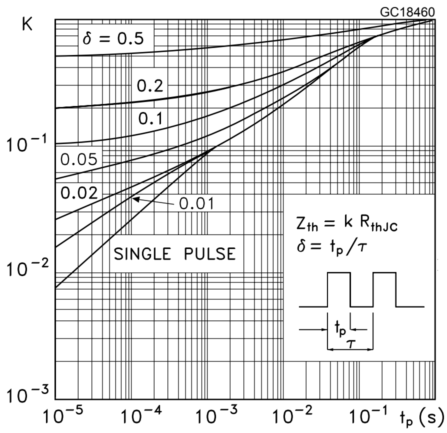


Figure 27. Normalized transient thermal impedance for diode



3 Test circuits

Figure 28. Test circuit for inductive load switching

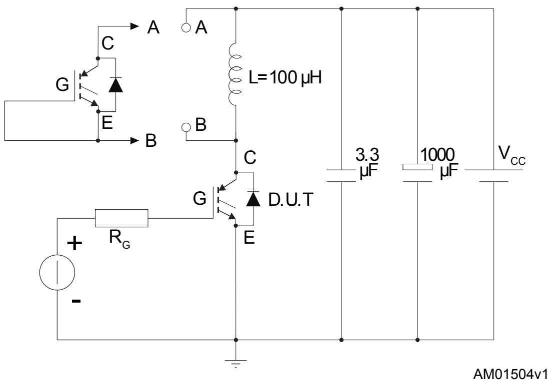


Figure 29. Gate charge test circuit

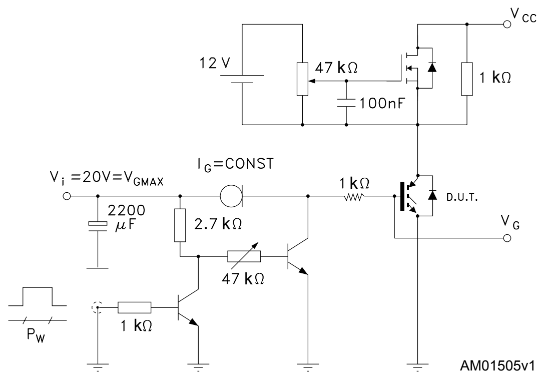


Figure 30. Switching waveform

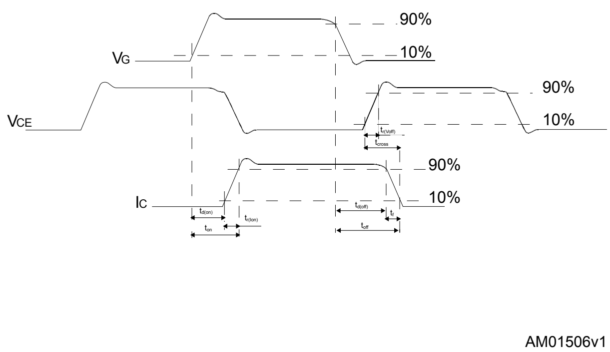
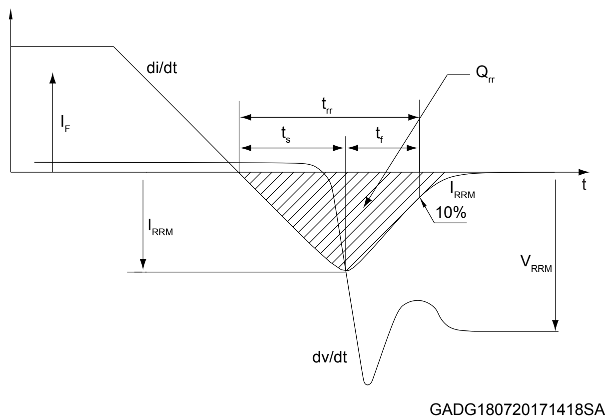


Figure 31. Diode reverse recovery waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 Max247 long leads package information

Figure 32. Max247 long leads package outline

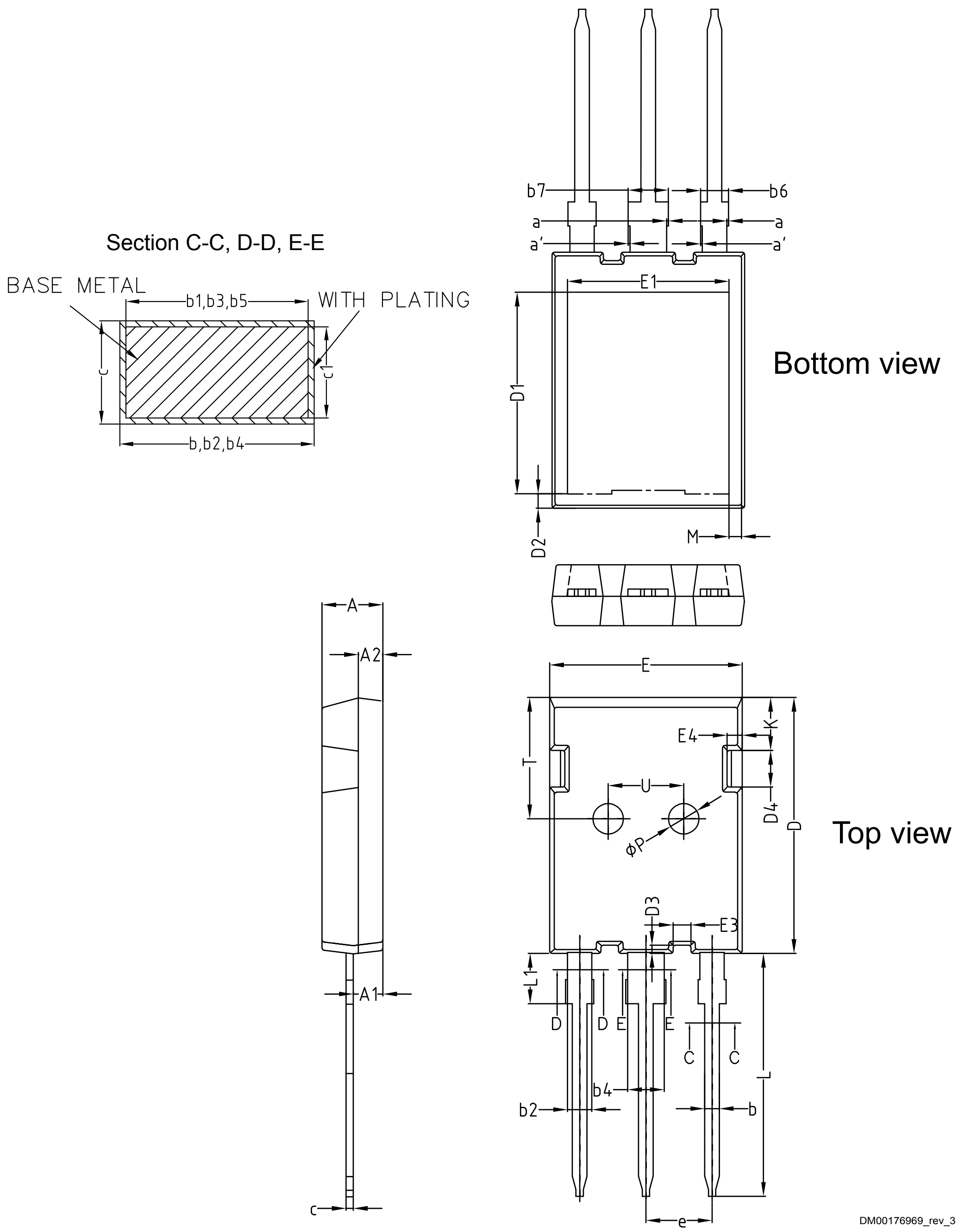


Table 7. **Max247 long leads package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0		0.15
a'	0		0.15
b	1.16		1.26
b1	1.15	1.20	1.22
b2	1.96		2.06
b3	1.95	2.00	2.02
b4	2.96		3.06
b5	2.95	3.00	3.02
b6			2.25
b7			3.25
c	0.59		0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
D3	0.58	0.68	0.78
D4	2.90	3.00	3.10
E	15.70	15.80	15.90
E1	13.10	13.26	13.50
E3	1.35	1.45	1.55
E4	1.14	1.24	1.34
e	5.34	5.44	5.54
K	4.25	4.35	4.45
L	19.80	19.92	20.10
L1	3.90		4.30
M	0.70		1.30
P	2.40	2.50	2.60
T	9.80		10.20
U	6.00		6.40

Revision history

Table 8. Document revision history

Date	Revision	Changes
06-Apr-2016	1	First release.
10-May-2016	2	Document status promoted to production data. Added *Section 2.1: "Electrical characteristics (curves)"*
15-Jun-2016	3	Updated *Figure 1: "Internal schematic diagram"* and *Table 2: "Absolute maximum ratings".* Updated *Section 2.1: "Electrical characteristics (curves)".* Minor text changes.
12-Aug-2016	4	Updated *Table 7: "Diode switching characteristics (inductive load)"* and *Figure 25: Reverse recovery charge vs. diode current slope".* Minor text changes.
13-Sep-2017	5	Updated title, features and application in cover page. Updated *Figure 13: "Normalized V(BR)CES vs. junction temperature".* Minor text changes.
07-Feb-2023	6	Updated Section 4.1 Max247 long leads package information. Minor text changes.

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